

8Kx8 Power-Switched and Reprogrammable PROM

Features

- · CMOS for optimum speed/power
- · Windowed for reprogrammability
- · High speed
 - 20 ns (Commercial)
- · Low power
 - 660 mW (Commercial)
- · Super low standby power
- Less than 85 mW when deselected
- EPROM technology 100% programmable
- 5V ±10% V_{CC}, commercial and military
- TTL-compatible I/O
- Direct replacement for 27C64 EPROMs

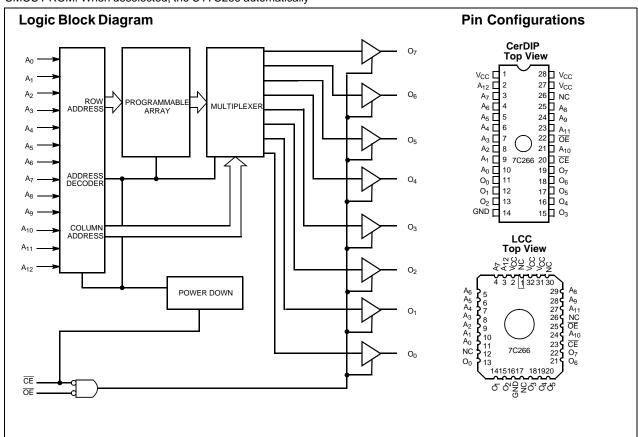
Functional Description

The CY7C266 is a high-performance 8192-word by 8-bit CMOS PROM. When deselected, the CY7C266 automatically

powers down into a low-power standby mode. It is packaged in a 600-mil-wide package. The reprogrammable packages are equipped with an erasure window; when exposed to UV light, these PROMs are erased and can then be reprogrammed. The memory cells utilize proven EPROM technology floating-gate and byte-wide intelligent programming algorithms.

The CY7C266 is a plug-in replacement for EPROM devices. The EPROM cell requires only 12.5V for the super voltage and low-current requirements allow for gang programming. The EPROM cells allow for each memory location to be tested 100%, as each location is written into, erased, and repeatedly exercised prior to encapsulation. Each PROM is also tested for AC performance to guarantee that after customer programming, the product will meet DC and AC specification

Reading is accomplished by placing an active LOW signal on OE and CE. The contents of the memory location addressed by the address lines (A_0 through A_{12}) will become available on the output lines (O_0 through O_7).



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Selection Guide

		7C266-20	7C266-25	7C266-45	Unit
Maximum Access Time		20	25	45	ns
Maximum Operating Current	Commercial	120	120	100	mA
Maximum Standby Current	Commercial	15	15	15	mA

Maximum Ratings[1]

(Above which the useful life may be impaired. For user guidelines, not tested.) Storage Temperature-65°C to +150°C Ambient Temperature with Power Applied.......55°C to +125°C Supply Voltage to Ground Potential (Pin 28 to Pin 14)-0.5V to +7.0V DC Voltage Applied to Outputs in High Z State-0.5V to +7.0V DC Input Voltage......-3.0V to +7.0V

DC Program Voltage	13.0V
Static Discharge Voltage(per MIL-STD-883, Method 3015)	> 2001V
Latch-Up Current	> 200 mA
UV Exposure	. 7258 Wsec/cm ²

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	5V ± 10%

Electrical Characteristics Over the Operating Range^[2]

Parameter	Description	Test Conditions		7C2	66-20	7C2	66-25	Unit
rarameter	neter Description Test Conditions		Min.	Max.	Min.	Max.	Oilit	
V _{OH}	Output HIGH Voltage	V _{CC} = Min.,	Com'l	2.4		2.4		V
		$I_{OH} = -2.0 \text{ mA}$				2.4		
V _{OL}	Output LOW Voltage	$V_{CC} = Min., I_{OL} = 8.0 \text{ mA}$	Com'l		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.0		2.0		V
V _{IL}	Input LOW Voltage				0.8		0.8	V
I _{IX}	Input Current	$GND \le V_{IN} \le V_{CC}$		-10	+10	-10	+10	μΑ
V _{CD}	Input Diode Clamp Voltage				No	te 3		
I _{OZ}	Output Leakage Current	V _{OL} ≤ V _{OUT} ≤ V _{OH} , Output Disabled		-40	+40	-40	+40	μА
I _{OS}	Output Short Circuit Current ^[3]	V _{CC} = Max., V _{OUT} = GND	-20	-90	-20	-90	mA	
I _{CC}	Power Supply Current	$V_{CC} = Max., V_{IN} = 2.0V,$ Com'l $I_{OUT} = 0 \text{ mA}$			120		120	mA
I _{SB}	Standby Supply Current	Chip Enable Inactive, CE ≥ V _{IH} , I _{OUT} = 0 mA		15		15	mA	

Notes

- The voltage on any input or I/O pin cannot exceed the power pin during power-up.
 See the "Introduction to CMOS PROMs" section of the Cypress Data Book for general information on testing.
 For test purposes, not more than one output at a time should be shorted. Short circuit test duration should not exceed 30 seconds.

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Electrical Characteristics Over the Operating Range^[2] (continued)

Parameter	Description	Test Conditions		7C26	6-45	Unit
rarameter	Description	rest Conditions		Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0 \text{ mA}$		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 16.0 mA			0.4	V
V _{IH}	Input HIGH Voltage			2.0		V
V _{IL}	Input LOW Voltage					
I _{IX}	Input Current	$GND \le V_{IN} \le V_{CC}$	-10	+10	mA	
V _{CD}	Input Diode Clamp Voltage		Note 3			
I _{OZ}	Output Leakage Current	V _{OL} ≤ V _{OUT} ≤ V _{OH} , Output Disabled	-10	+10	mA	
I _{OS}	Output Short Circuit Current ^[3]	$V_{CC} = Max., V_{OUT} = GND$	-20	-90	mA	
I _{CC}	Power Supply Current	$V_{CC} = Max., V_{IN} = 2.0V,$ $I_{OUT} = 0 \text{ mA}$			100	mA
I _{SB}	Standby Supply Current				15	mA

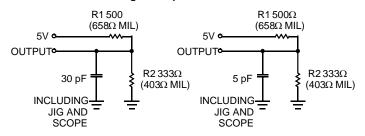
Capacitance^[2]

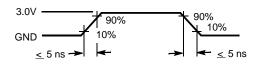
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.0V$	10	pF



AC Test Loads and Waveforms

Test Load for -20 through -25 speeds

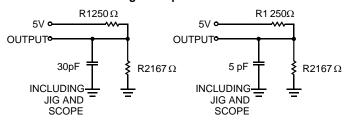




(a) Normal Load

(b) High Z Load

Test Load for -35 through -45 speeds



(c) Normal Load

(d) High Z Load

Equivalent to: THÉ VENIN EQUIVALENT

OUTPUT O $R_{TH} 100\Omega$ O 2.0V

Switching Characteristics Over the Operating Range^[2]

Doromotor	Description	7C2	66-20	7C26	66-25	7C266-45		Unit	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Onit	
t _{AA}	Address to Output Valid		20		25		45	ns	
t _{HZCE}	Chip Enable Inactive to High Z		25		30		45	ns	
t _{HZOE}	Output Enable Inactive to High Z		12		12		20	ns	
t _{AOE}	Output Enable Active to Output Valid		12		12		20	ns	
t _{ACE}	Chip Enable Active to Output Valid		25		30		45	ns	
t _{OHA}	Data Hold from Address Change	3		3		3		ns	
t _{PU}	Chip Enable Active to Power-up		25		30		45	ns	
t _{PD}	Chip Enable Inactive to Power-down		25		30		45	ns	

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Erasure Characteristics

Wavelengths of light less than 4000 angstroms begin to erase the devices in the windowed package. For this reason, an opaque label should be placed over the window if the EPROM is exposed to sunlight or fluorescent lighting for extended periods of time.

The recommended dose of ultraviolet light for erasure is a wavelength of 2537 angstroms for a minimum dose (UV intensity multiplied by exposure time) of 25 Wsec/cm². For an ultraviolet lamp with a 12 mW/cm² power rating, the exposure time would be approximately 35 minutes. The CY7C266 needs to be within 1 inch of the lamp during erasure. Permanent damage may

result if the EPROM is exposed to high-intensity UV light for an extended period of time.

7258 Wsec/cm2 is the recommended maximum dosage.

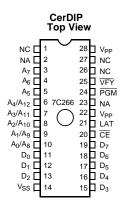
Programming Modes

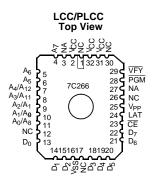
Programming support is available from Cypress as well as from a number of third party software vendors. For detailed programming information, including a listing of software packages, please see the PROM Programming Information located at the end of this section. Programming algorithms can be obtained from any Cypress representative.

Table 1. Mode Selection

					Pin F	unction ^{[4}	l, 5]		
Mode	Normal Operation	A ₈	A ₉	A ₁₀	A ₁₁	A ₁₂	CE	OE	D ₇ –D ₀
•	Program	VFY	PGM	LAT	NA	NA	CE	V _{PP}	D ₇ D ₀
Read		A ₈	A ₉	A ₁₀	A ₁₁	A ₁₂	V _{IL}	V _{IL}	O ₇ -O ₀
Standby		Х	Х	Х	Х	Х	V _{IH}	Х	Three-Stated
Output D	Disable	A ₈	A ₉	A ₁₀	A ₁₁	A ₁₂	V _{IL}	V _{IH}	Three-Stated
Program	1	V_{IHP}	V_{ILP}	V _{ILP}	V _{ILP}	V_{ILP}	V _{ILP}	V_{PP}	D ₇ D ₀
Program	n Verify	V_{ILP}	V _{IHP}	V_{ILP}	V _{ILP}	V_{ILP}	V_{ILP}	V_{PP}	O ₇ O ₀
Program	n Inhibit	V_{IHP}	V _{IHP}	V_{ILP}	V _{ILP}	V_{ILP}	V_{ILP}	V_{PP}	Three-Stated
Blank Cl	heck	V _{ILP}	V _{IHP}	V _{ILP}	V _{ILP}	V _{ILP}	V _{ILP}	V _{PP}	O ₇ -O ₀

Figure 1. Programming Pinout



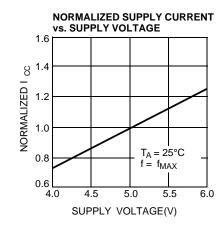


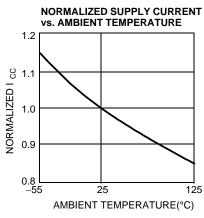
Notes

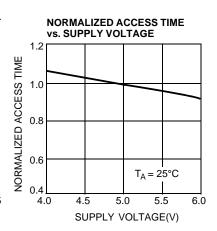
- 4. X = "don't care" but must not exceed $V_{CC} + 5$ %.
- 5. Address A_8 – A_{12} must be latched through lines A_0 – A_4 in Programming modes.

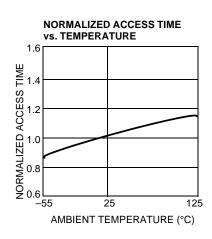


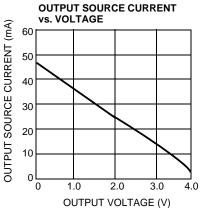
Typical DC and AC Characteristics

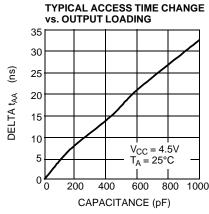


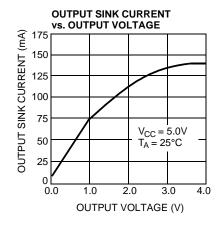


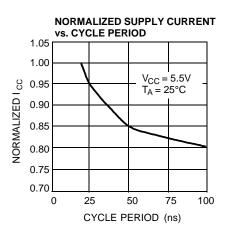












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Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C266-20JC	J64	28-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C266-20WC	W16	28-Lead (600-Mil) Windowed CerDIP	

Package Diagrams

Figure 2. 28-Lead(600-Mil) CerDIP D16

MIL-STD-1835 D-10 Config. A

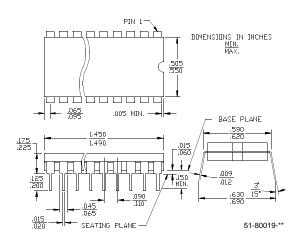




Figure 3. 32-Pin Rectangular Leadless Chip Carrier L55

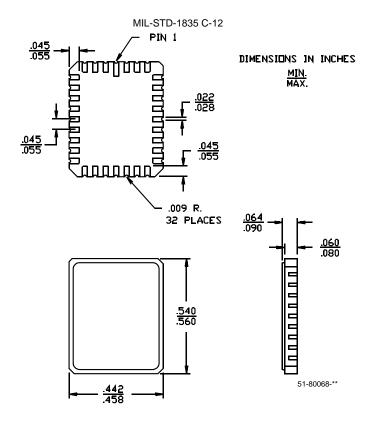




Figure 4. 28LD(600 MIL) PDIP Package Outline

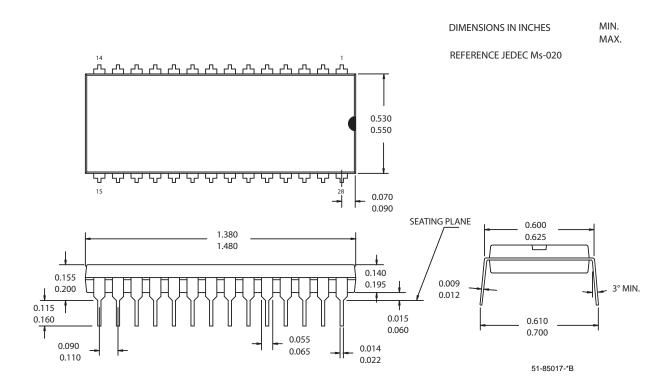




Figure 5. 32-Pin Windowed Rectangular Leadless Chip Carrier Q55

MIL-STD-1835 C-12

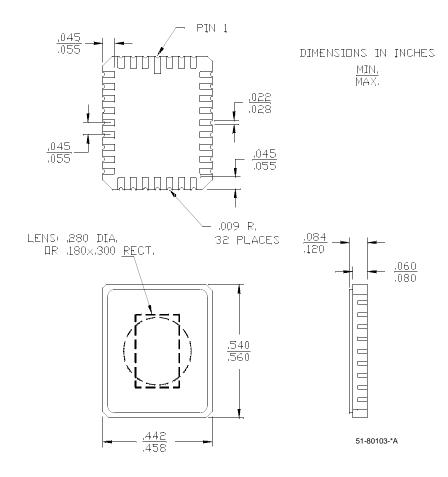
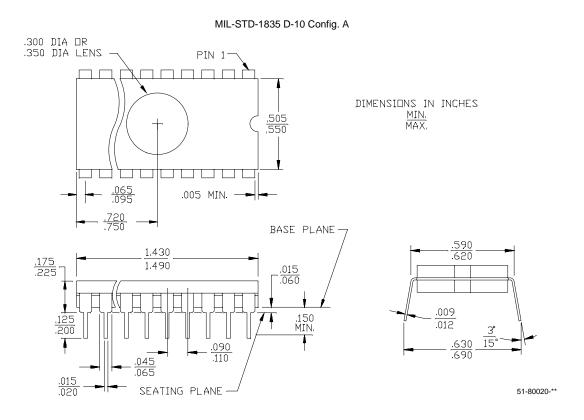




Figure 6. 28-Lead (600-Mil) Windowed CerDIP W16



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Document History Page

Document Title: CY7C266 8K x 8 Power Switched and Reprogrammable PROM Document Number: 38-04005							
REV. ECN NO. Issue Date Orig. of Change Description of Change				Description of Change			
**	113861	03/08/02	DSG	Changed from Spec number: 38-00086 to 38-04005			
*A	118897	10/09/02	GBI	Updated ordering information			
*B	122246	12/27/02	RBI	Added power up requirements to Operating Conditions Information			
*C	499538	See ECN	PCI	Updated ordering information			